Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1027	438/592.ccls.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF ·	2006/04/27 16:49
L2	1338	438/592.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/27 17:13
L3	606	438/591.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/27 17:26
L4	900	438/595.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/27 17:37
L5	389	438/216.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/27 17:45
L6	564	438/299.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/27 16:55
L7	1322	438/301.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/27 16:55
L8 .	1307	438/303.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF .	2006/04/27 16:55
S1 ·	4	metal adj gate and gate adj insulating adj layer and capping adj layer	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/10 11:54
S2	43	metal adj gate and gate adj oxide and capping adj layer	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/08 14:09

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S3	7	metal adj gate and capping adj layer and selective adj oxidation	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/08 14:37
S4	30	metal adj gate and capping adj layer and oxid\$7 same silicon adj substrate	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/08 14:55
S5	6	metal adj gate and capping adj layer and oxidizing same silicon adj substrate	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/08 15:48
S6	2	metal adj gate and capping adj layer and selective adj oxidation same silicon adj substrate	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/09 12:31
S7	7	gate and capping adj layer and selective adj oxidation same silicon adj substrate	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR .	ON	2004/11/08 17:37
S8	9	("5573961" "5631179" "5736455" "5766998" "5851927" "5869359" "6075274" "6136658" "6162741").PN.	USPAT	OR .	OFF	2004/11/08 16:53
S9	17	gate and capping adj layer and selective adj oxidation	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/08 17:37
S10	20	metal adj gate and selective adj oxidation same silicon adj substrate	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/09 12:49
S11	8	metal adj gate and selective adj oxidation same silicon adj substrate and "H.sub.2 O" and "H. sub.2"	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/09 12:40
S12	2	("4505028").PN.	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/09 12:54
S13		metal adj gate and silicon adj oxide adj layer and selective adj oxidation	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/10 13:03

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S15	118	gate and capping adj layer and selective near5 oxid\$7	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 11:26
S16	· 55	gate and capping adj layer and selective near5 oxid\$7 and silicon adj oxide	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 12:42
S17	25	gate and capping adj layer same silicon adj oxide and selective near5 oxid\$7	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 14:52
S18	638	Metal adj gate and source/drain adj region	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 14:54
S19	318	Metal adj gate and source/drain adj region and oxidation	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 14:55
S20	17	Metal adj gate and source/drain adj region and reoxidation	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 17:58
S21	245	"100" adj nm and metal adj gate and width	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 18:03
S22	3	"100" adj nm same metal adj gate same width	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 18:16
S23	5	"100" adj nm same metal adj gate same width	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 18:17
S24	2	("6277722").PN.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 10:43
S25	2	("4505028").PN.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 11:17
S26	6.26.E0 PM	("6245605").PN.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/05 11:18

S27	2	("6245605").PN.	USPAT;	OR	OFF	2005/05/11 18:58
			EPO; JPO; DERWENT;			
			IBM_TDB			